

DESCRIPTION:

With high ability to withstand the shock loading of large current, TYN1225C SCR provides high dV/dt rate with strong resistance to electromagnetic interference. It is especially recommended for use on solid state relay, motorcycle, power charger, T-tools etc. Package TO-220C is RoHS compliant.

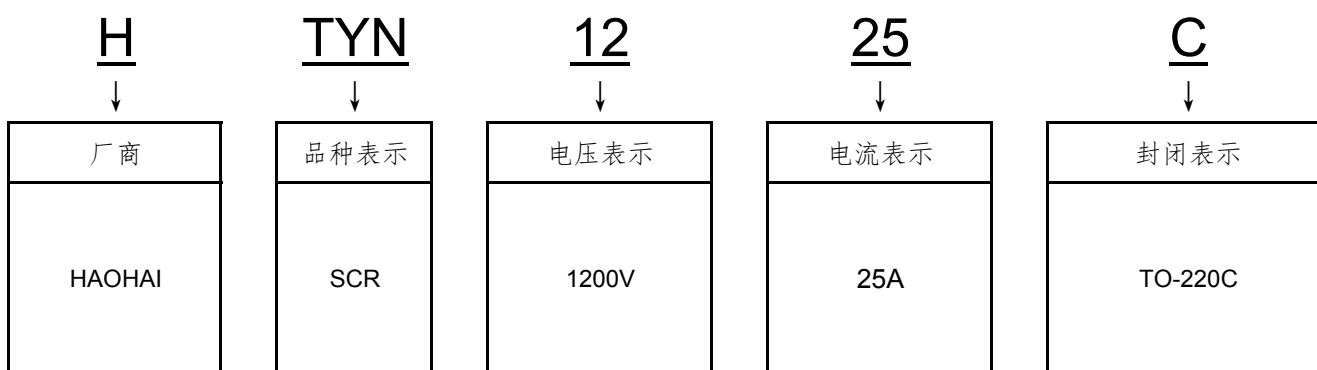
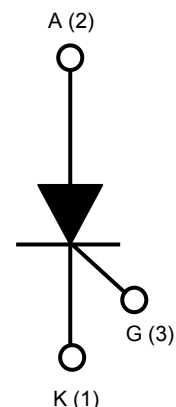
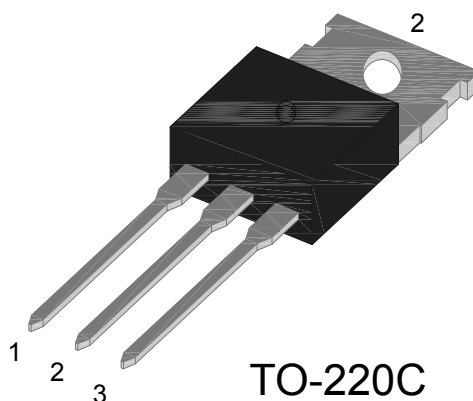
Product Model Reference & Naming

25A	产品型号列表、对应封装、型号对照电压值					I _{GT}
	封装标识	600V	800V	1000V	1200V	
TO-220C	C	TYN625C	TYN825C	TYN1025C	TYN1225C	≤40mA
Remarks		标准品种	高压品种	特制高压	特制高压	

PINNING: Insulated Package

Pin in Symbol and Description			
1	K	Cathode	阴极
2	A	Anode	阳极
3	G	Gate	门-控制极
4		Tab	散热片

Pin Polarity Diagram
脚位与极性 电路符号表示



■ ABSOLUTE RATINGS (Limiting Values)

SYMBOL	Parameter & Test Conditions		Value	Unit
$I_{T(RMS)}$	RMS on-state current	$T_C \leq 85^\circ\text{C}$	25	A
I_{TSM}	Non repetitive surge peak on-state current	$t_p=10\text{ms}, T_J=25^\circ\text{C}$	320	
		$t_p=8.3\text{ms}, T_J=25^\circ\text{C}$	352	
$I_{T(AV)}$	Average on-state current	$T_C \leq 85^\circ\text{C}$	16	
I_{GM}	Peak gate current	$t_p=20\mu\text{s}, T_J=125^\circ\text{C}$	5	
I^2t	I^2t value for fusing	$t_p=10\text{ms}, T_J=25^\circ\text{C}$	512	A^2s
P_{GM}	Peak gate power	$T_J=125^\circ\text{C}$	20	W
$P_{G(AV)}$	Average gate power dissipation	$T_J=125^\circ\text{C}$	1	
V_{DRM}	Repetitive peak off-state voltage	$T_J=25^\circ\text{C}$	1200	V
V_{RRM}	Repetitive peak reverse voltage	$T_J=25^\circ\text{C}$		
di/dt	Critical rate of rise of on-state current	$I_G=2 \times I_{GT}, f=100\text{Hz}, T_J=125^\circ\text{C}$	200	$\text{A}/\mu\text{s}$
V_{PP}	Peak pulse voltage ($T_J=25^\circ\text{C}$, non-repetitive, off-state, FIG.7)		1	kV
T_J	Operating Junction Temperature Range		-40~+125	$^\circ\text{C}$
T_{stg}	Storage Temperature Range		-40~+150	

■ ELECTRICAL CHARACTERISTICS ($T_J=25^\circ\text{C}$ Unless Otherwise Noted)

SYMBOL	Parameter & Test Conditions	Min	Typ	Max	Unit
I_{GT}	$V_D=12\text{V}, R_L=33\Omega$	--	--	40	mA
I_H	Holding Current ($I_T=500\text{mA}$)	--	--	80	
I_L	$I_G=1.2 I_{GT}$	--	--	90	
V_{GT}	$V_D=12\text{V}, R_L=33\Omega$	--	--	1	V
V_{GD}	$V_D=V_{DRM}, T_J=125^\circ\text{C}, R_L=3.3\text{K}\Omega$	0.2	--	--	
dV/dt	$V_D=800\text{V}$, Gate Open $T_J=125^\circ\text{C}$	1000	--	--	$\text{V}/\mu\text{s}$
t_{on}	$I_G=50\text{mA}, I_A=500\text{mA}, I_R=50\text{mA}, T_J=25^\circ\text{C}$	--	5	--	μs
t_{off}		--	70	--	

■ STATIC CHARACTERISTICS

SYMBOL	Parameter & Test Conditions	Max	Unit
V_{TM}	$I_{TM}=50\text{A}, t_p=380\mu\text{s}$	$T_J=25^\circ\text{C}$ 1.55	V
V_{TO}	Threshold voltage	$T_J=125^\circ\text{C}$ 0.74	
R_D	Dynamic resistance	$T_J=125^\circ\text{C}$ 19	$\text{m}\Omega$
I_{DRM}	$V_D=V_{DRM}, V_R=V_{RRM}$	$T_J=25^\circ\text{C}$ 7	μA
I_{RRM}	$V_D=V_{DRM}, V_R=V_{RRM}$	$T_J=125^\circ\text{C}$ 2	mA

■ THERMAL RESISTANCES

SYMBOL	Parameter	Value	Unit
$R_{th(j-c)}$	Junction to case (DC)	0.9	$^\circ\text{C}/\text{W}$
$R_{th(j-a)}$	Junction to ambient (DC)	45	

Voltage Current Characteristic of SCR

FIG-1: Maximum power dissipation versus RMS on-state current

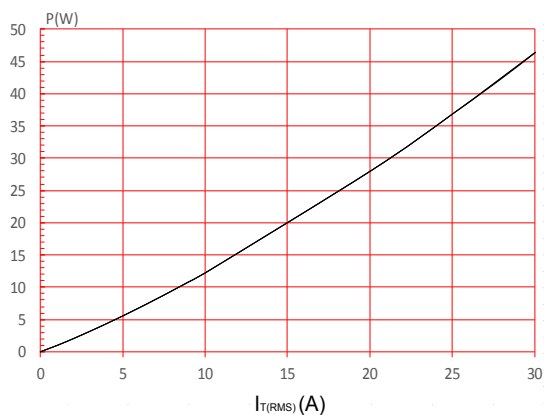


FIG-2: RMS on-state current versus case temperature

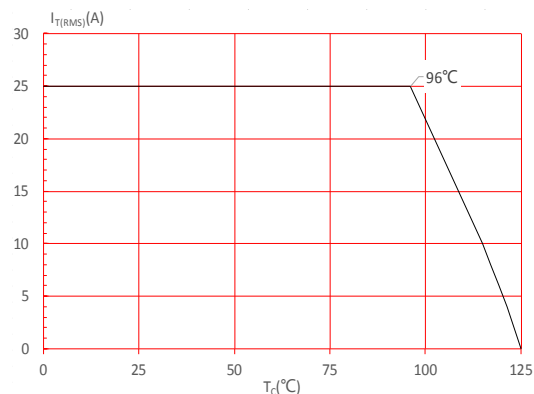


FIG-3: Surge peak on-state current versus number of cycles

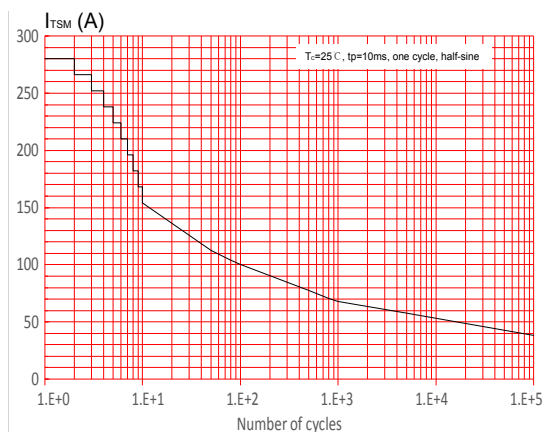


FIG-4: On-state characteristics

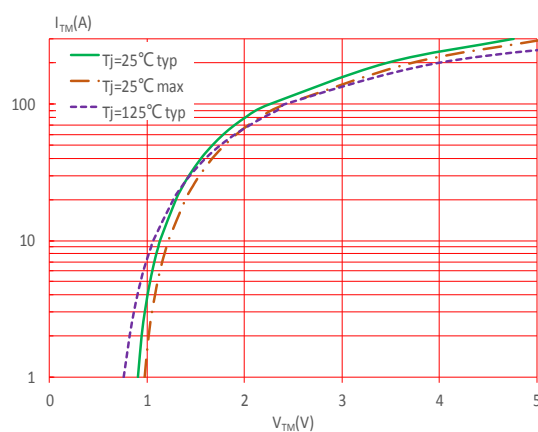


FIG-5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$, and corresponding value of I^2t ($di/dt < 200\text{A}/\mu\text{s}$)

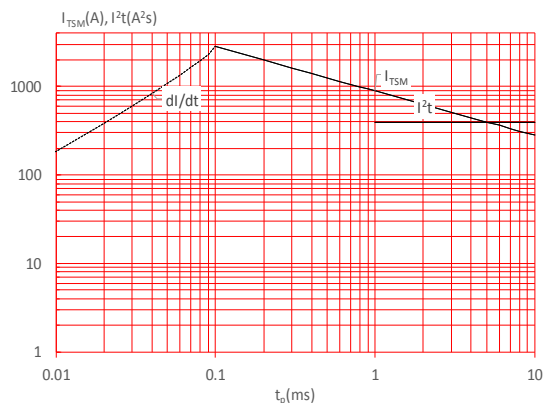


FIG-6: Relative variations of gate trigger current, holding current and latching current versus junction temperature

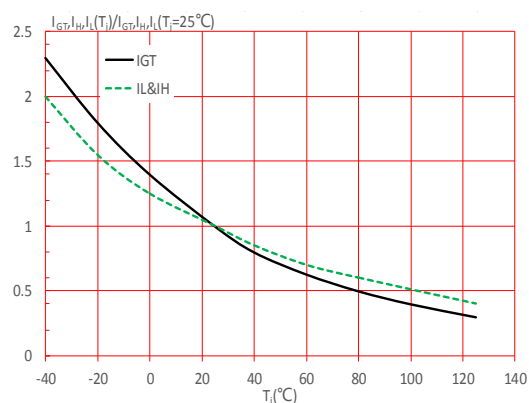
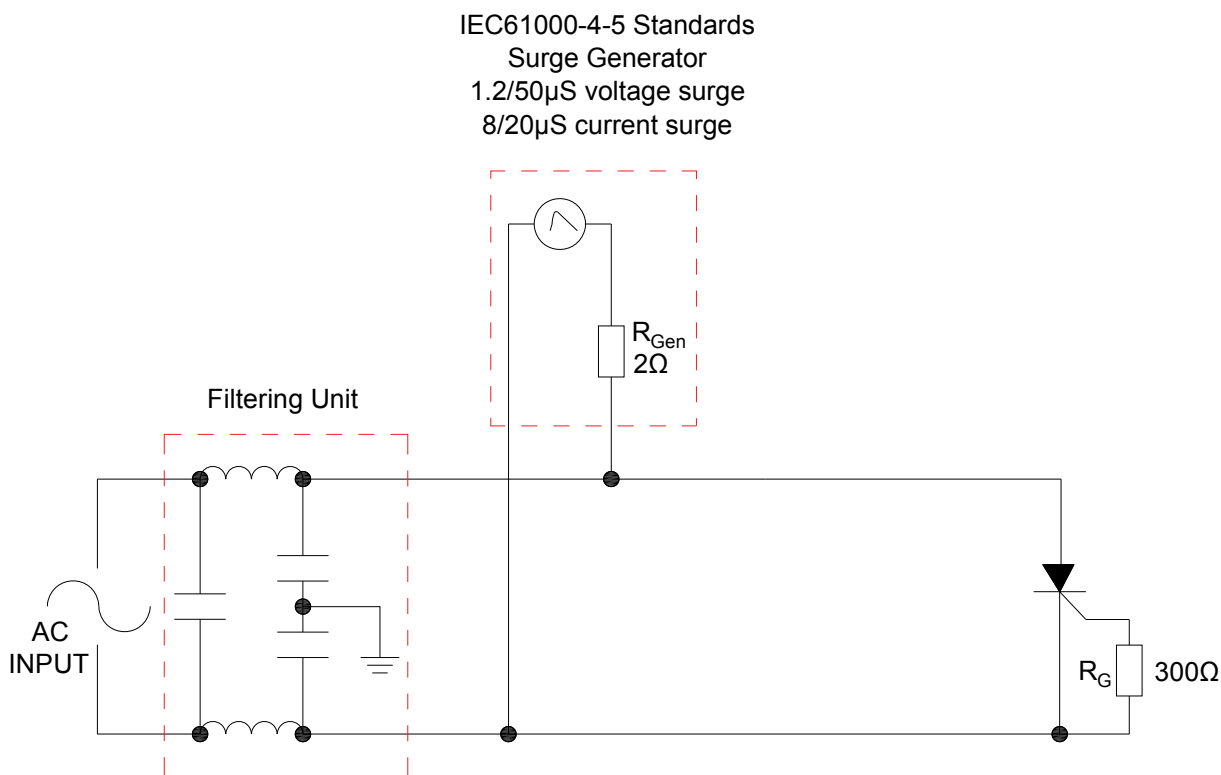


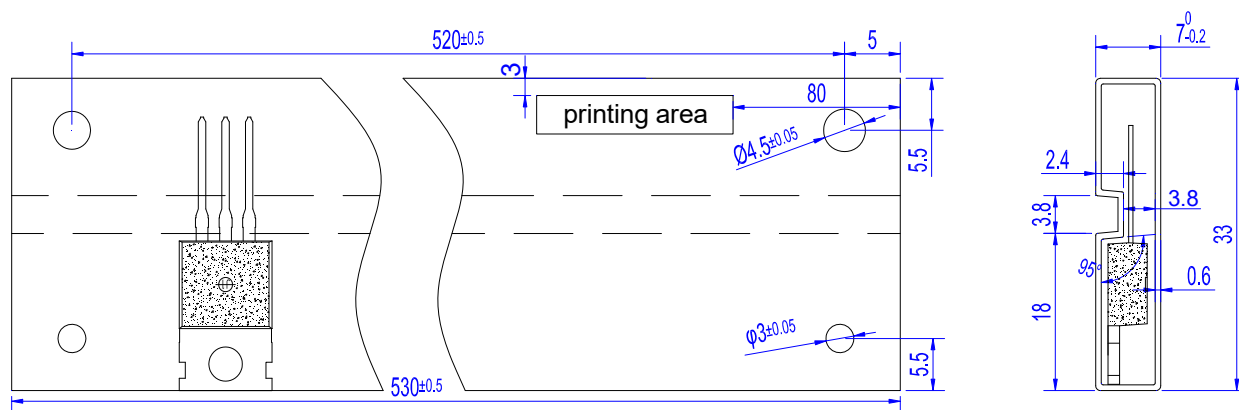
FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



TO-220C PACKAGE MECHANICAL DATA (mm & inch)

REF	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
B	0.70	0.90	0.028	0.035
C	0.45	0.60	0.018	0.024
C2	1.25	1.35	0.049	0.053
C3	2.20	2.60	0.087	0.102
D	8.90	9.90	0.350	0.390
E	9.90	10.3	0.390	0.406
F	6.30	6.90	0.248	0.272
G	2.40	2.70	0.094	0.106
H	28.0	29.8	1.102	1.173
L1	2.70	3.30	0.106	0.130
L2	1.14	1.70	0.045	0.067
L3	2.65	2.95	0.104	0.116

DELIVERY MODE



■ Packaging Specifications

PACKAGE	OUTLINE	REF.	Tube.	BOX	Carton
TO-220C	TUBE	QTY	50 Pcs	1,000 Pcs	5,000 Pcs

Manufacturers version information

2006-07-01, KKG™ Product Data-1.0

2010-04-01, KKG™ Product Data-1.1

2014-12-01, KKG™ Product Data-1.2

2020-09-16, KKG™ Product Data-1.3

2023-12-29, KKG™ Product Data-1.4



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